

# Mauritius C M Van De Sanden

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

457 papers	16,784 citations	64 h-index	109 g-index
478 ext. papers	18,415 ext. citations	3.6 avg, IF	6.65 L-index

#	Paper	IF	Citations
457	Observation and rationalization of nitrogen oxidation enabled only by coupled plasma and catalyst.. <i>Nature Communications</i> , <b>2022</b> , 13, 402	17.4	1
456	The Chemical Origins of Plasma Contraction and Thermalization in CO Microwave Discharges.. <i>Journal of Physical Chemistry Letters</i> , <b>2022</b> , 1203-1208	6.4	0
455	Plasma Driven Exsolution for Nanoscale Functionalization of Perovskite Oxides.. <i>Small Methods</i> , <b>2021</b> , 5, e2100868	12.8	4
454	Plasma Activated Electrochemical Ammonia Synthesis from Nitrogen and Water. <i>ACS Energy Letters</i> , <b>2021</b> , 6, 313-319	20.1	16
453	Revisiting spontaneous Raman scattering for direct oxygen atom quantification. <i>Optics Letters</i> , <b>2021</b> , 46, 2172-2175	3	5
452	High-Throughput Computational Screening of Cubic Perovskites for Solid Oxide Fuel Cell Cathodes. <i>Journal of Physical Chemistry Letters</i> , <b>2021</b> , 12, 4160-4165	6.4	3
451	Resolving discharge parameters from atomic oxygen emission. <i>Plasma Sources Science and Technology</i> , <b>2021</b> , 30, 065022	3.5	0
450	Operando attenuated total reflection Fourier-transform infrared (ATR-FTIR) spectroscopy for water splitting. <i>Journal Physics D: Applied Physics</i> , <b>2021</b> , 54, 133001	3	2
449	Electrochemical Activation of Atomic Layer-Deposited Cobalt Phosphate Electrocatalysts for Water Oxidation. <i>ACS Catalysis</i> , <b>2021</b> , 11, 2774-2785	13.1	13
448	Operational Strategies to Improve the Performance and Long-Term Cyclability of Intermediate Temperature Sodium-Sulfur Batteries. <i>ChemElectroChem</i> , <b>2021</b> , 8, 1156-1166	4.3	4
447	Flame bands: CO + O chemiluminescence as a measure of gas temperature. <i>Journal Physics D: Applied Physics</i> , <b>2021</b> , 54, 374005	3	1
446	Redefining the Microwave Plasma-Mediated CO <sub>2</sub> Reduction Efficiency Limit: The Role of O <sub>2</sub> Association. <i>ACS Energy Letters</i> , <b>2021</b> , 6, 2876-2881	20.1	3
445	Rational Design of Photoelectrodes for the Fully Integrated Polymer Electrode Membrane Photoelectrochemical Water-Splitting System: A Case Study of Bismuth Vanadate. <i>ACS Applied Energy Materials</i> , <b>2021</b> , 4, 9600-9610	6.1	1
444	Emission spectroscopy of He lines in high-density plasmas in Magnum-PSI. <i>AIP Advances</i> , <b>2020</b> , 10, 025225	5.5	4
443	Insight into contraction dynamics of microwave plasmas for CO <sub>2</sub> conversion from plasma chemistry modelling. <i>Plasma Sources Science and Technology</i> , <b>2020</b> , 29, 105014	3.5	9
442	Plasma activation of N <sub>2</sub> , CH <sub>4</sub> and CO <sub>2</sub> : an assessment of the vibrational non-equilibrium time window. <i>Plasma Sources Science and Technology</i> , <b>2020</b> , 29, 115001	3.5	7
441	Mode resolved heating dynamics in pulsed microwave CO <sub>2</sub> plasma from laser Raman scattering. <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 054002	3	12

440	Symmetrical Exsolution of Rh Nanoparticles in Solid Oxide Cells for Efficient Syngas Production from Greenhouse Gases. <i>ACS Catalysis</i> , <b>2020</b> , 10, 1278-1288	13.1	26
439	Implications of thermo-chemical instability on the contracted modes in CO <sub>2</sub> microwave plasmas. <i>Plasma Sources Science and Technology</i> , <b>2020</b> , 29, 025005	3.5	26
438	Charge carrier dynamics and photocatalytic activity of {111} and {100} faceted AgPO particles. <i>Journal of Chemical Physics</i> , <b>2020</b> , 152, 244710	3.9	2
437	CO <sub>2</sub> Conversion in Nonuniform Discharges: Disentangling Dissociation and Recombination Mechanisms. <i>Journal of Physical Chemistry C</i> , <b>2020</b> , 124, 16806-16819	3.8	17
436	Enhancing the Electrocatalytic Activity of Redox Stable Perovskite Fuel Electrodes in Solid Oxide Cells by Atomic Layer-Deposited Pt Nanoparticles. <i>ACS Sustainable Chemistry and Engineering</i> , <b>2020</b> , 8, 12646-12654	8.3	8
435	Validation of the Fokker-Planck Approach to Vibrational Kinetics in CO <sub>2</sub> Plasma. <i>Journal of Physical Chemistry C</i> , <b>2019</b> , 123, 22823-22831	3.8	16
434	Atmospheric-pressure silica-like thin film deposition using 200 kHz/13.56 MHz dual frequency excitation. <i>Journal Physics D: Applied Physics</i> , <b>2019</b> , 52, 355201	3	4
433	Electrochemistry of Sputtered Hematite Photoanodes: A Comparison of Metallic DC versus Reactive RF Sputtering. <i>ACS Omega</i> , <b>2019</b> , 4, 9262-9270	3.9	4
432	Numerical model for the determination of the reduced electric field in a CO <sub>2</sub> microwave plasma derived by the principle of impedance matching. <i>Plasma Sources Science and Technology</i> , <b>2019</b> , 28, 075016	3.5	13
431	High and intermediate temperature sodium-sulfur batteries for energy storage: development, challenges and perspectives.. <i>RSC Advances</i> , <b>2019</b> , 9, 5649-5673	3.7	50
430	Excitation and relaxation of the asymmetric stretch mode of CO <sub>2</sub> in a pulsed glow discharge. <i>Plasma Sources Science and Technology</i> , <b>2019</b> , 28, 035011	3.5	18
429	Plasma-Activated Electrolysis for Cogeneration of Nitric Oxide and Hydrogen from Water and Nitrogen. <i>ACS Energy Letters</i> , <b>2019</b> , 4, 2091-2095	20.1	18
428	Co-electrolysis of H <sub>2</sub> O and CO <sub>2</sub> on exsolved Ni nanoparticles for efficient syngas generation at controllable H <sub>2</sub> /CO ratios. <i>Applied Catalysis B: Environmental</i> , <b>2019</b> , 258, 117950	21.8	29
427	Role of Electron-Ion Dissociative Recombination in (hbox {CH}_4) Microwave Plasma on Basis of Simulations and Measurements of Electron Energy. <i>Plasma Chemistry and Plasma Processing</i> , <b>2019</b> , 39, 1275-1289	3.6	3
426	Solar Hydrogen Generation from Ambient Humidity Using Functionalized Porous Photoanodes. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 41267-41280	9.5	8
425	Characterization of CO <sub>2</sub> microwave plasma based on the phenomenon of skin-depth-limited contraction. <i>Plasma Sources Science and Technology</i> , <b>2019</b> , 28, 115022	3.5	17
424	Observation of Nanoparticle Exsolution from Perovskite Oxides: From Atomic Scale Mechanistic Insight to Nanostructure Tailoring. <i>ACS Nano</i> , <b>2019</b> , 13, 12996-13005	16.7	78
423	Fokker-Planck equation for chemical reactions in plasmas. <i>Rendiconti Lincei</i> , <b>2019</b> , 30, 25-30	1.7	2

422 28. Plasma-based CO<sub>2</sub> conversion **2019**, 585-634

2

421 The importance of thermal dissociation in CO<sub>2</sub> microwave discharges investigated by power pulsing and rotational Raman scattering. *Plasma Sources Science and Technology*, **2019**, 28, 055015 3.5 39

420 An Electrochemical Study on the Cathode of the Intermediate Temperature Tubular Sodium-Sulfur (NaS) Battery. *Journal of the Electrochemical Society*, **2019**, 166, A135-A142 3.9 14

419 Atomic layer deposition of cobalt phosphate thin films for the oxygen evolution reaction. *Electrochemistry Communications*, **2019**, 98, 73-77 5.1 18

418 The role of carrier gas flow in roll-to-roll AP-PECVD synthesized silica moisture barrier films. *Surface and Coatings Technology*, **2018**, 339, 20-26 4.4 5

417 Preferential vibrational excitation in microwave nitrogen plasma assessed by Raman scattering. *Plasma Sources Science and Technology*, **2018**, 27, 055006 3.5 17

416 Atmospheric-pressure diffuse dielectric barrier discharges in Ar/O<sub>2</sub> gas mixture using 200 kHz/13.56 MHz dual frequency excitation. *Journal Physics D: Applied Physics*, **2018**, 51, 114002 3 10

415 Improving uniformity of atmospheric-pressure dielectric barrier discharges using dual frequency excitation. *Plasma Sources Science and Technology*, **2018**, 27, 01LT01 3.5 7

414 A rotational Raman study under non-thermal conditions in a pulsed CO<sub>2</sub> glow discharge. *Plasma Sources Science and Technology*, **2018**, 27, 045009 3.5 16

413 Plasma for electrification of chemical industry: a case study on CO<sub>2</sub> reduction. *Plasma Physics and Controlled Fusion*, **2018**, 60, 014019 2 43

412 Plasma radiation studies in Magnum-PSI using resistive bolometry. *Nuclear Fusion*, **2018**, 58, 106006 3.3 10

411 How the alternating degeneracy in rotational Raman spectra of CO and CH reveals the vibrational temperature. *Applied Optics*, **2018**, 57, 5694-5702 1.7 9

410 Plasma conductivity as a probe for ambient air admixture in an atmospheric pressure plasma jet. *Plasma Chemistry and Plasma Processing*, **2018**, 38, 63-74 3.6 1

409 The role of the gradient film properties in silica moisture barriers synthesized in a roll-to-roll atmospheric pressure plasma enhanced CVD reactor. *Plasma Processes and Polymers*, **2018**, 15, 1700093 3.4 10

408 Visible detection of performance controlling pinholes in silica encapsulation films. *Journal Physics D: Applied Physics*, **2018**, 51, 43LT01 3 1

407 Numerical simulation of atmospheric-pressure 200 kHz/13.56 MHz dual-frequency dielectric barrier discharges. *Plasma Sources Science and Technology*, **2018**, 27, 105016 3.5 8

406 Non-oxidative methane coupling to C<sub>2</sub> hydrocarbons in a microwave plasma reactor. *Plasma Processes and Polymers*, **2018**, 15, 1800087 3.4 18

405 Vibrational Kinetics in Plasma as a Functional Problem: A Flux-Matching Approach. *Journal of Physical Chemistry A*, **2018**, 122, 7918-7923 2.8 16

404	Mechanisms of elementary hydrogen ion-surface interactions during multilayer graphene etching at high surface temperature as a function of flux. <i>Carbon</i> , <b>2018</b> , 137, 527-532	10.4	6
403	Zeolites for CO-CO-O Separation to Obtain CO-Neutral Fuels. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 20512-20520	9.5	20
402	Variable roughness development in statically deposited SiO <sub>2</sub> thin films: a spatially resolved surface morphology analysis. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 285303	3	2
401	Nanostructuring of iron thin films by high flux low energy helium plasma. <i>Thin Solid Films</i> , <b>2017</b> , 631, 50-56	2.2	7
400	Defect prevention in silica thin films synthesized using AP-PECVD for flexible electronic encapsulation. <i>Journal Physics D: Applied Physics</i> , <b>2017</b> , 50, 25LT01	3	6
399	Atomic layer deposition of highly dispersed Pt nanoparticles on a high surface area electrode backbone for electrochemical promotion of catalysis. <i>Electrochemistry Communications</i> , <b>2017</b> , 84, 40-44	5.1	14
398	Time evolution of vibrational temperatures in a CO <sub>2</sub> glow discharge measured with infrared absorption spectroscopy. <i>Plasma Sources Science and Technology</i> , <b>2017</b> , 26, 115008	3.5	41
397	Atomistic simulations of graphite etching at realistic time scales. <i>Chemical Science</i> , <b>2017</b> , 8, 7160-7168	9.4	3
396	Fast nanostructured carbon microparticle synthesis by one-step high-flux plasma processing. <i>Carbon</i> , <b>2017</b> , 124, 403-414	10.4	5
395	Atomic hydrogen induced defect kinetics in amorphous silicon. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2017</b> , 35, 05C307	2.9	5
394	The 2017 Plasma Roadmap: Low temperature plasma science and technology. <i>Journal Physics D: Applied Physics</i> , <b>2017</b> , 50, 323001	3	496
393	Infrared gas phase study on plasma-polymer interactions in high-current diffuse dielectric barrier discharge. <i>Journal of Applied Physics</i> , <b>2017</b> , 121, 243301	2.5	5
392	Oscillatory vapour shielding of liquid metal walls in nuclear fusion devices. <i>Nature Communications</i> , <b>2017</b> , 8, 192	17.4	28
391	Insight into CO <sub>2</sub> Dissociation in Plasma from Numerical Solution of a Vibrational Diffusion Equation. <i>Journal of Physical Chemistry C</i> , <b>2017</b> , 121, 19568-19576	3.8	31
390	Control of the intrinsic microstructure in AP-PECVD synthesised amorphous silica thin films. <i>RSC Advances</i> , <b>2017</b> , 7, 52274-52282	3.7	1
389	An analytical force balance model for dust particles with size up to several Debye lengths. <i>Physics of Plasmas</i> , <b>2017</b> , 24, 113702	2.1	3
388	On the synergistic effect of inorganic/inorganic barrier layers: An ellipsometric porosimetry investigation. <i>Plasma Processes and Polymers</i> , <b>2017</b> , 14, 1700012	3.4	2
387	Homogeneous CO <sub>2</sub> conversion by microwave plasma: Wave propagation and diagnostics. <i>Plasma Processes and Polymers</i> , <b>2017</b> , 14, 1600120	3.4	70

- 386 Atmospheric pressure roll-to-roll plasma enhanced CVD of high quality silica-like bilayer encapsulation films. *Plasma Processes and Polymers*, **2017**, 14, 1600143 3.4 19
- 385 Plasma-driven dissociation of CO<sub>2</sub> for fuel synthesis. *Plasma Processes and Polymers*, **2017**, 14, 1600126 3.4 113
- 384 The electrochemistry of iron oxide thin films nanostructured by high ion flux plasma exposure. *Electrochimica Acta*, **2017**, 258, 709-717 6.7 13
- 383 Non-equilibrium Microwave Plasma for Efficient High Temperature Chemistry. *Journal of Visualized Experiments*, **2017**, 1.6 2
- 382 Synergy Between Plasma-Assisted ALD and Roll-to-Roll Atmospheric Pressure PE-CVD Processing of Moisture Barrier Films on Polymers. *Plasma Processes and Polymers*, **2016**, 13, 311-315 3.4 13
- 381 Self-Regulated Plasma Heat Flux Mitigation Due to Liquid Sn Vapor Shielding. *Physical Review Letters*, **2016**, 116, 135002 7.4 42
- 380 Molecular dynamics simulations of ballistic He penetration into W fuzz. *Nuclear Fusion*, **2016**, 56, 1260153.3 16
- 379 CO<sub>2</sub>-Neutral Fuels. *Europhysics News*, **2016**, 47, 22-26 0.2 21
- 378 Gas-Phase Plasma Synthesis of Free-Standing Silicon Nanoparticles for Future Energy Applications. *Plasma Processes and Polymers*, **2016**, 13, 19-53 3.4 14
- 377 Analysis of temporal evolution of quantum dot surface chemistry by surface-enhanced Raman scattering. *Scientific Reports*, **2016**, 6, 29508 4.9 9
- 376 Fluid modelling of CO<sub>2</sub> dissociation in a dielectric barrier discharge. *Journal of Applied Physics*, **2016**, 119, 093301 2.5 58
- 375 Dielectric barrier discharges revisited: the case for mobile surface charge. *Plasma Sources Science and Technology*, **2016**, 25, 03LT03 3.5 10
- 374 In situ spectroscopic ellipsometry during atomic layer deposition of Pt, Ru and Pd. *Journal Physics D: Applied Physics*, **2016**, 49, 115504 3 24
- 373 Oxygen Evolution at Hematite Surfaces: The Impact of Structure and Oxygen Vacancies on Lowering the Overpotential. *Journal of Physical Chemistry C*, **2016**, 120, 18201-18208 3.8 97
- 372 Back Cover: Plasma Process. Polym. **2016**. *Plasma Processes and Polymers*, **2016**, 13, 202-202 3.4 1
- 371 Expanding Thermal Plasma Deposition of Al-Doped ZnO: On the Effect of the Plasma Chemistry on Film Growth Mechanisms. *Plasma Processes and Polymers*, **2016**, 13, 54-69 3.4 4
- 370 Improved size distribution control of silicon nanocrystals in a spatially confined remote plasma. *Plasma Sources Science and Technology*, **2015**, 24, 015030 3.5 3
- 369 The impact of the nano-pore filling on the performance of organosilicon-based moisture barriers. *Thin Solid Films*, **2015**, 595, 251-257 2.2 11

368	The relation between the production efficiency of nitrogen atoms and the electrical characteristics of a dielectric barrier discharge. <i>Plasma Sources Science and Technology</i> , <b>2015</b> , 24, 045006	3.5	15
367	Note: Rotational Raman scattering on CO <sub>2</sub> plasma using a volume Bragg grating as a notch filter. <i>Review of Scientific Instruments</i> , <b>2015</b> , 86, 046106	1.7	20
366	Gas temperature in transient CO <sub>2</sub> plasma measured by Raman scattering. <i>Journal Physics D: Applied Physics</i> , <b>2015</b> , 48, 155201	3	16
365	Residual gas entering high density hydrogen plasma: rarefaction due to rapid heating. <i>Plasma Sources Science and Technology</i> , <b>2015</b> , 24, 025020	3.5	4
364	Taming microwave plasma to beat thermodynamics in CO <sub>2</sub> dissociation. <i>Faraday Discussions</i> , <b>2015</b> , 183, 233-48	3.6	128
363	Waveguide Nanowire Superconducting Single-Photon Detectors Fabricated on GaAs and the Study of Their Optical Properties. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2015</b> , 21, 1-10	3.8	157
362	Surface modifications induced by high fluxes of low energy helium ions. <i>Scientific Reports</i> , <b>2015</b> , 5, 9779	4.9	33
361	Characterization of Nanocrystal Size Distribution using Raman Spectroscopy with a Multi-particle Phonon Confinement Model. <i>Journal of Visualized Experiments</i> , <b>2015</b> , e53026	1.6	2
360	Towards Roll-to-Roll Deposition of High Quality Moisture Barrier Films on Polymers by Atmospheric Pressure Plasma Assisted Process. <i>Plasma Processes and Polymers</i> , <b>2015</b> , 12, 545-554	3.4	41
359	Relation between light trapping and surface topography of plasma textured crystalline silicon wafers. <i>Progress in Photovoltaics: Research and Applications</i> , <b>2015</b> , 23, 352-366	6.8	7
358	The influence of partial surface discharging on the electrical characterization of DBDs. <i>Plasma Sources Science and Technology</i> , <b>2015</b> , 24, 015016	3.5	37
357	Spontaneous synthesis of carbon nanowalls, nanotubes and nanotips using high flux density plasmas. <i>Carbon</i> , <b>2014</b> , 68, 695-707	10.4	18
356	An improved thin film approximation to accurately determine the optical conductivity of graphene from infrared transmittance. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 013105	3.4	8
355	Nanostructuring of iron surfaces by low-energy helium ions. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2014</b> , 6, 3462-8	9.5	31
354	On the role of nanoporosity in controlling the performance of moisture permeation barrier layers. <i>Microporous and Mesoporous Materials</i> , <b>2014</b> , 188, 163-171	5.3	34
353	CO and byproduct formation during CO <sub>2</sub> reduction in dielectric barrier discharges. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 123303	2.5	77
352	Nucleation of silicon nanocrystals in a remote plasma without subsequent coagulation. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 244301	2.5	10
351	On the intrinsic moisture permeation rate of remote microwave plasma-deposited silicon nitride layers. <i>Thin Solid Films</i> , <b>2014</b> , 558, 54-61	2.2	22

350	High throughput deposition of hydrogenated amorphous carbon coatings on rubber with expanding thermal plasma. <i>Surface and Coatings Technology</i> , <b>2014</b> , 245, 74-83	4.4	9
349	Direct ion flux measurements at high-pressure-depletion conditions for microcrystalline silicon deposition. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 063305	2.5	19
348	Efficient plasma route to nanostructure materials: case study on the use of m-WO <sub>3</sub> for solar water splitting. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2013</b> , 5, 7621-5	9.5	84
347	Direct characterization of nanocrystal size distribution using Raman spectroscopy. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 134310	2.5	51
346	Morphological Description of Ultra-Smooth Organo-Silicone Layers Synthesized Using Atmospheric Pressure Dielectric Barrier Discharge Assisted PECVD. <i>Plasma Processes and Polymers</i> , <b>2013</b> , 10, 313-319	3.4	13
345	Ultrahigh throughput plasma processing of free standing silicon nanocrystals with lognormal size distribution. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 134306	2.5	35
344	Carbon monoxide-induced reduction and healing of graphene oxide. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2013</b> , 31, 040601	2.9	13
343	Chemical sputtering of graphite by low temperature nitrogen plasmas at various substrate temperatures and ion flux densities. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 133301	2.5	7
342	On the effect of the underlying ZnO:Al layer on the crystallization kinetics of hydrogenated amorphous silicon. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 212107	3.4	2
341	Substrate-biasing during plasma-assisted atomic layer deposition to tailor metal-oxide thin film growth. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2013</b> , 31, 01A106	2.9	77
340	Evidence of the filling of nano-porosity in SiO <sub>2</sub> -like layers by an initiated-CVD monomer. <i>Microporous and Mesoporous Materials</i> , <b>2012</b> , 151, 434-439	5.3	28
339	Kinetic study of solid phase crystallisation of expanding thermal plasma deposited a-Si:H. <i>Thin Solid Films</i> , <b>2012</b> , 520, 5820-5825	2.2	5
338	The Relation Between the Bandgap and the Anisotropic Nature of Hydrogenated Amorphous Silicon. <i>IEEE Journal of Photovoltaics</i> , <b>2012</b> , 2, 94-98	3.7	25
337	Reaction mechanisms of atomic layer deposition of TaN <sub>x</sub> from Ta(NMe <sub>2</sub> ) <sub>5</sub> precursor and H <sub>2</sub> -based plasmas. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2012</b> , 30, 01A101	2.9	21
336	Gas-phase hydrosilylation of plasma-synthesized silicon nanocrystals with short- and long-chain alkynes. <i>Langmuir</i> , <b>2012</b> , 28, 17295-301	4	19
335	Improved conductivity of aluminum-doped ZnO: The effect of hydrogen diffusion from a hydrogenated amorphous silicon capping layer. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 063715	2.5	9
334	Controlling the resistivity gradient in aluminum-doped zinc oxide grown by plasma-enhanced chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 043708	2.5	9
333	Remote plasma deposition of microcrystalline silicon thin-films: Film structure and the role of atomic hydrogen. <i>Journal of Non-Crystalline Solids</i> , <b>2012</b> , 358, 379-386	3.9	10

332	Synergistic etch rates during low-energetic plasma etching of hydrogenated amorphous carbon. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 013302	2.5	13
331	Plasma Atomic Layer Deposition <b>2012</b> , 131-157		5
330	Real time in situ spectroscopic ellipsometry of the growth and plasmonic properties of au nanoparticles on SiO <sub>2</sub> . <i>Nano Research</i> , <b>2012</b> , 5, 513-520	10	34
329	Atomic layer deposition for nanostructured Li-ion batteries. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2012</b> , 30, 010801	2.9	102
328	Detailed H(n= 2) density measurements in a magnetized hydrogen plasma jet. <i>Plasma Sources Science and Technology</i> , <b>2012</b> , 21, 024009	3.5	5
327	Surface passivation of phosphorus-diffused n+-type emitters by plasma-assisted atomic-layer deposited Al <sub>2</sub> O <sub>3</sub> . <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2012</b> , 6, 4-6	2.5	67
326	Hydrogenated amorphous silicon p <sub>in</sub> solar cells deposited under well controlled ion bombardment using pulse-shaped substrate biasing. <i>Progress in Photovoltaics: Research and Applications</i> , <b>2012</b> , 20, 333-342	6.8	5
325	Plasma-enhanced Chemical Vapor Deposition of Aluminum Oxide Using Ultrashort Precursor Injection Pulses. <i>Plasma Processes and Polymers</i> , <b>2012</b> , 9, 761-771	3.4	13
324	Surface Dynamics of SiO <sub>2</sub> -like Films on Polymers Grown by DBD Assisted CVD at Atmospheric Pressure. <i>Plasma Processes and Polymers</i> , <b>2012</b> , 9, 1194-1207	3.4	15
323	In situ crystallization kinetics studies of plasma-deposited, hydrogenated amorphous silicon layers. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 033508	2.5	9
322	Ion-induced effects on grain boundaries and a-Si:H tissue quality in microcrystalline silicon films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2012</b> , 30, 061512	2.9	5
321	Initiated-chemical vapor deposition of organosilicon layers: Monomer adsorption, bulk growth, and process window definition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2012</b> , 30, 041503	2.9	25
320	Solid-phase crystallization of ultra high growth rate amorphous silicon films. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 103510	2.5	8
319	Influence of annealing and Al <sub>2</sub> O <sub>3</sub> properties on the hydrogen-induced passivation of the Si/SiO <sub>2</sub> interface. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 093713	2.5	112
318	Microfocus infrared ellipsometry characterization of air-exposed graphene flakes. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 061909	3.4	14
317	Substrate Biasing during Plasma-Assisted ALD for Crystalline Phase-Control of TiO <sub>2</sub> Thin Films. <i>Electrochemical and Solid-State Letters</i> , <b>2011</b> , 15, G1-G3		41
316	Er <sup>3+</sup> and Si luminescence of atomic layer deposited Er-doped Al <sub>2</sub> O <sub>3</sub> thin films on Si(100). <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 113107	2.5	21
315	On the oxidation mechanism of microcrystalline silicon thin films studied by Fourier transform infrared spectroscopy. <i>Journal of Non-Crystalline Solids</i> , <b>2011</b> , 357, 884-887	3.9	23

3 <sup>14</sup>	Improved adhesion and tribological properties of fast-deposited hard graphite-like hydrogenated amorphous carbon films. <i>Diamond and Related Materials</i> , <b>2011</b> , 20, 1266-1272	3.5	12
3 <sup>13</sup>	Excellent Si surface passivation by low temperature SiO <sub>2</sub> using an ultrathin Al <sub>2</sub> O <sub>3</sub> capping film. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2011</b> , 5, 22-24	2.5	63
3 <sup>12</sup>	Plasma-Assisted Deposition of Au/SiO <sub>2</sub> Multi-layers as Surface Plasmon Resonance-Based Red-Colored Coatings. <i>Plasmonics</i> , <b>2011</b> , 6, 255-260	2.4	12
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3 <sup>01</sup>	Influence of the Oxidant on the Chemical and Field-Effect Passivation of Si by ALD Al <sub>2</sub> O <sub>3</sub> . <i>Electrochemical and Solid-State Letters</i> , <b>2011</b> , 14, H1		131
3 <sup>00</sup>	Dielectric Properties of Thermal and Plasma-Assisted Atomic Layer Deposited Al <sub>2</sub> O <sub>3</sub> Thin Films. <i>Journal of the Electrochemical Society</i> , <b>2011</b> , 158, G21	3.9	53
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